Silicon PNP Power Transistors 2SA653

DESCRIPTION

·With TO-66 package

·High voltage: V_{CEO}=-120V(min)

APPLICATIONS

·Low frequency power amplifier color TV vertical deflection output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-1.0	A
P_C	Collector power dissipation	T_C=25□	15	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA ;I_B=0	-120			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-1mA ;I_E=0	-150			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-0.5A; I_B=-50mA			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-0.5A; I_B=-50mA			-2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-150V; I_E=0			-10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-10	μA
h_{FE}	DC current gain	I_C=-0.2A ; V_{CE}=-5V	40			
f_T	Transition frequency	I_C=-0.1A ; V_{CE}=-10V		15		MHz

PACKAGE OUTLINE

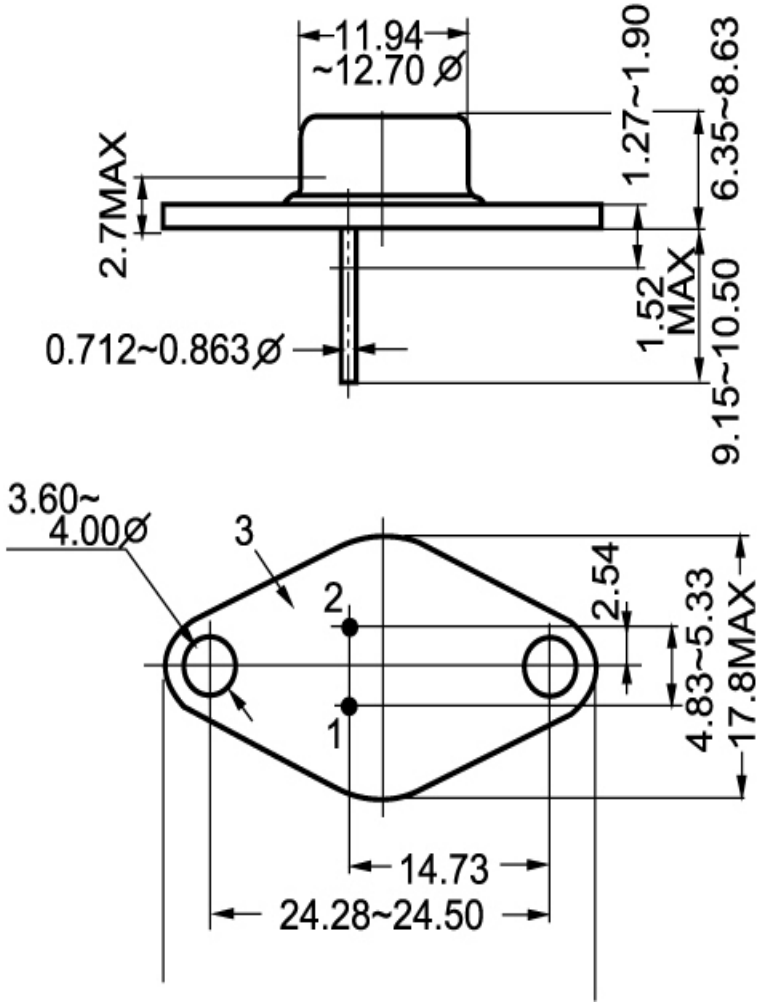

Fig.2 outline dimensions